

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
18	BRS	L18	0	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) near3 (single adj2 symbol or one adj2 symbol or first adj1 symbol) near3 (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:51	
19	BRS	L19	1	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) with (single adj2 symbol or one adj2 symbol or first adj1 symbol) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:53	
20	BRS	L20	1	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) with (single adj2 symbol or one adj2 symbol or first adj1 symbol or symbol adj2 interval or symbol adj2 period) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:57	

	Error Definition	Err ors
18		
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	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	3	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) near3 (digital adj2 signal) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3 or "N" adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:58	

	Error Definition	Err ors
21		



# PALM INTRANET

Day : Monday  
Date: 6/5/2006  
Time: 18:13:51

## Inventor Name Search Result

Your Search was:

Last Name = LEE

First Name = SEUNG-HWAN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">08671245</a>	<a href="#">5790542</a>	150	06/27/1996	DESTINATION ADDRESS DETECTION APPARATUS FOR HARDWARE PACKET ROUTER	LEE, SEUNG- HWAN
<a href="#">09036356</a>	<a href="#">6218260</a>	150	03/06/1998	METHODS OF FORMING INTEGRATED CIRCUIT CAPACITORS HAVING IMPROVED ELECTRODE AND DIELECTRIC LAYER CHARACTERISTICS AND CAPACITORS FORMED THEREBY	LEE, SEUNG- HWAN
<a href="#">09083350</a>	<a href="#">6077573</a>	150	05/22/1998	PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION METHODS OF FORMING HEMISPHERICAL GRAINED SILICON LAYERS	LEE, SEUNG- HWAN
<a href="#">09168096</a>	Not Issued	161	10/08/1998	METHOD OF FABRICATING A CAPACITOR WITH A LOWER ELECTRODE HAVING AN UNEVEN SURFACE AN UPPER ELECTRODE WITH VARYING IMPURITY CONCENTRATIONS	LEE, SEUNG- HWAN
<a href="#">09190390</a>	Not Issued	161	11/10/1998	METHOD FOR FORMING CAPACITOR USING HEMISPHERICAL GRAIN SILICON LAYER BY SELECTIVE DEPOSITION PROCESS	LEE, SEUNG- HWAN
<a href="#">09535949</a>	Not Issued	161	03/27/2000	Semiconductor device and method for manufacturing the same	LEE, SEUNG- HWAN
<a href="#">09735244</a>	<a href="#">6624069</a>	150	12/12/2000	METHODS OF FORMING INTEGRATED CIRCUIT CAPACITORS HAVING DOPED HSG ELECTRODES	LEE, SEUNG- HWAN
<a href="#">09862367</a>	<a href="#">6448146</a>	150	05/22/2001	METHODS OF MANUFACTURING INTEGRATED CIRCUIT CAPACITORS HAVING HEMISPHERICAL GRAIN	LEE, SEUNG- HWAN

				ELECTRODES	
<u>09871430</u>	<u>6468924</u>	150	05/31/2001	METHODS OF FORMING THIN FILMS BY ATOMIC LAYER DEPOSITION	LEE, SEUNG-HWAN
<u>09872203</u>	<u>6828218</u>	150	05/31/2001	METHOD OF FORMING A THIN FILM USING ATOMIC LAYER DEPOSITION	LEE, SEUNG-HWAN
<u>09886142</u>	<u>6391803</u>	150	06/20/2001	METHOD OF FORMING SILICON CONTAINING THIN FILMS BY ATOMIC LAYER DEPOSITION UTILIZING TRISDIMETHYLAMINOSILANE	LEE, SEUNG-HWAN
<u>09887547</u>	Not Issued	161	06/22/2001	Internet service provider server system, method of providing data, method of advertising using moving pictures, and recording media therefor	LEE, SEUNG-HWAN
<u>09887554</u>	Not Issued	160	06/22/2001	Internet service provider server system, method of providing data, method of advertising using moving pictures, and recording media therefor	LEE, SEUNG-HWAN
<u>09902607</u>	<u>6833310</u>	150	07/12/2001	SEMICONDUCTOR DEVICE HAVING THIN FILM FORMED BY ATOMIC LAYER DEPOSITION AND METHOD FOR FABRICATING THE SAME	LEE, SEUNG-HWAN
<u>10012116</u>	<u>6828616</u>	150	11/13/2001	INTEGRATED CIRCUIT DEVICES THAT UTILIZE DOPED POLY-SI1-XGEX CONDUCTIVE PLUGS AS INTERCONNECTS	LEE, SEUNG-HWAN
<u>10026618</u>	Not Issued	71	12/27/2001	Digital communication synchronization system and method thereof	LEE, SEUNG-HWAN
<u>10034043</u>	<u>6599807</u>	150	12/20/2001	METHOD FOR MANUFACTURING CAPACITOR OF SEMICONDUCTOR DEVICE HAVING IMPROVED LEAKAGE CURRENT CHARACTERISTICS	LEE, SEUNG-HWAN
<u>10102653</u>	<u>6639554</u>	150	03/22/2002	APPARATUS AND METHOD FOR TRACKING LOCATION OF MOBILE STATION	LEE, SEUNG-HWAN
<u>10127651</u>	<u>6893915</u>	150	04/22/2002	SEMICONDUCTOR DEVICE HAVING BARRIER LAYER BETWEEN RUTHENIUM LAYER AND METAL LAYER AND METHOD FOR MANUFACTURING THE SAME	LEE, SEUNG-HWAN
<u>10201784</u>	<u>6531388</u>	150	07/25/2002	METHOD OF FORMING AN	LEE, SEUNG-

				ALUMINUM FILM FOR USE IN MANUFACTURING A SEMICONDUCTOR DEVICE	HWAN
<u>10293317</u>	Not Issued	41	11/13/2002	Apparatus and method for receiving digital signal	LEE, SEUNG-HWAN
<u>10322945</u>	Not Issued	41	12/18/2002	Apparatus and method for digital symbol synchronization	LEE, SEUNG-HWAN
<u>10403572</u>	<u>6933245</u>	150	03/31/2003	METHOD OF FORMING A THIN FILM WITH A LOW HYDROGEN CONTENT ON A SEMICONDUCTOR DEVICE	LEE, SEUNG-HWAN
<u>10452431</u>	Not Issued	30	05/30/2003	Voice recognition device, observation probability calculating device, complex fast fourier transform calculation device and method, cache device, and method of controlling the cache device	LEE, SEUNG-HWAN
<u>10616056</u>	Not Issued	41	07/09/2003	METHODS OF FORMING ELECTRONIC DEVICES INCLUDING DIELECTRIC LAYERS WITH DIFFERENT DENSITIES OF TITANIUM	LEE, SEUNG-HWAN
<u>10634244</u>	<u>6876029</u>	150	08/05/2003	INTEGRATED CIRCUIT CAPACITORS HAVING DOPED HSG ELECTRODES	LEE, SEUNG-HWAN
<u>10640244</u>	Not Issued	41	08/14/2003	Atomic layer deposition apparatus and method for preventing generation of solids in exhaust path	LEE, SEUNG-HWAN
<u>10793818</u>	Not Issued	93	03/08/2004	HIGH PERFORMANCE MIS CAPACITOR WITH HFO <sub>2</sub> DIELECTRIC	LEE, SEUNG-HWAN
<u>10795175</u>	Not Issued	93	03/05/2004	BIPOLAR DEVICE AND METHOD OF MANUFACTURING THE SAME INCLUDING PRE-TREATMENT USING GERMANE GAS	LEE, SEUNG-HWAN
<u>10806301</u>	Not Issued	93	03/22/2004	METHOD OF FABRICATING MOS TRANSISTOR USING TOTAL GATE SILICIDATION PROCESS	LEE, SEUNG-HWAN
<u>10823420</u>	<u>7033895</u>	150	04/13/2004	METHOD OF FABRICATING A MOS TRANSISTOR WITH ELEVATED SOURCE/DRAIN STRUCTURE USING A SELECTIVE EPITAXIAL GROWTH PROCESS	LEE, SEUNG-HWAN
<u>10851336</u>	<u>6987310</u>	150	05/24/2004	MULTI-LAYERED STRUCTURE INCLUDING AN EPITAXIAL LAYER HAVING A LOW	LEE, SEUNG-HWAN

				DISLOCATION DEFECT DENSITY, SEMICONDUCTOR DEVICE COMPRISING THE SAME, AND METHOD OF FABRICATING THE SEMICONDUCTOR DEVICE	
<u>10856155</u>	Not Issued	30	05/27/2004	Adaptive frequency control apparatus and method thereof	LEE, SEUNG-HWAN
<u>10884507</u>	Not Issued	71	07/02/2004	Methods of forming a multi-layered structure using an atomic layer deposition process and methods of forming a capacitor of an integrated circuit device	LEE, SEUNG-HWAN
<u>10917353</u>	Not Issued	30	08/13/2004	Sliding/hinge apparatus for sliding/rotating type mobile terminals	LEE, SEUNG-HWAN
<u>10942141</u>	Not Issued	41	09/16/2004	Swing-type portable digital communication apparatus and swing hinge device thereof	LEE, SEUNG-HWAN
<u>10951937</u>	Not Issued	71	09/28/2004	Apparatus and method for supplying a source, and method of depositing an atomic layer using the same	LEE, SEUNG-HWAN
<u>10968233</u>	Not Issued	41	10/19/2004	Methods of fabricating integrated circuit devices that utilize doped poly-Si1-xGex conductive plugs as interconnects	LEE, SEUNG-HWAN
<u>10977498</u>	7039124	150	11/01/2004	APPARATUS AND METHOD FOR COMPENSATING FOR ANALOG QUADRATURE MODULATION ERROR	LEE, SEUNG-HWAN
<u>10986018</u>	Not Issued	30	11/12/2004	At least penta-sided-channel type of FinFET transistor	LEE, SEUNG-HWAN
<u>10990429</u>	Not Issued	71	11/18/2004	Semiconductor device having thin film formed by atomic layer deposition and method for fabricating the same	LEE, SEUNG-HWAN
<u>11002571</u>	Not Issued	41	12/02/2004	Methods of forming capacitors with high dielectric layers and capacitors so formed	LEE, SEUNG-HWAN
<u>11037626</u>	Not Issued	30	01/18/2005	Trench capacitors with insulating layer collars in undercut regions and method of fabricating the same	LEE, SEUNG-HWAN
<u>11045060</u>	Not Issued	30	01/31/2005	Transistors for semiconductor device and methods of fabricating the same	LEE, SEUNG-HWAN
<u>11046876</u>	Not Issued	71	02/01/2005	Thin film structure, capacitor, and methods for forming the same	LEE, SEUNG-HWAN
<u>11059449</u>	Not Issued	30	02/17/2005	Methods of forming dielectric structures and capacitors	LEE, SEUNG-HWAN



<a href="#">11065086</a>	Not Issued	30	02/24/2005	Methods of forming a capacitor using an atomic layer deposition process	LEE, SEUNG-HWAN
<a href="#">11071018</a>	Not Issued	30	03/03/2005	Transistor and method of manufacturing the same	LEE, SEUNG-HWAN
<a href="#">11126251</a>	Not Issued	20	05/11/2005	Apparatus and method for compensating for an offset of a power amplifier in a mobile communication system	LEE, SEUNG-HWAN
<a href="#">11126253</a>	Not Issued	30	05/11/2005	Method and apparatus for estimating a sample delay between a transmission signal and a feedback signal in a mobile communication system, and a base station transmitter using the same	LEE, SEUNG-HWAN

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**Search Another: Inventor**

**Last Name**

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LEE

SEUNG-HWAN

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	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
18	BRS	L18	0	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) near3 (single adj2 symbol or one adj2 symbol or first adj1 symbol) near3 (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:51	
19	BRS	L19	1	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) with (single adj2 symbol or one adj2 symbol or first adj1 symbol) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 18:04	
20	BRS	L20	1	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) with (single adj2 symbol or one adj2 symbol or first adj1 symbol or symbol adj2 interval or symbol adj2 period) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:57	

	Error Definition	Err ors
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	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	3	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3) near3 (digital adj2 signal) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3 or "N" adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 17:58	
22	BRS	L22	1	(oversampl\$3 or resampl\$3 or re adj1 sampl\$3 or over adj1 sampl\$3 or interpolat\$4) with (single adj2 symbol or one adj2 symbol or first adj1 symbol or symbol near1 period or symbol near1 interval) with (plural\$3 adj2 sampl\$1 or multi adj2 sampl\$3 or plural\$3 adj2 subsampl\$1 or multi\$3 adj2 subsampl\$1 or first adj2 second adj2 subsampl\$3)	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 18:08	
23	BRS	L23	19	((SEUNG-HWAN) near2 (LEE)).INV.	USPAT	2006/06/0 5 18:08	
24	BRS	L24	0	23 and subsampl\$3 and symbol	US- PGPUB ; USPAT ; EPO; JPO	2006/06/0 5 18:10	
25	BRS	L25	3	((EUNG-BAE) near2 (KIM)).INV.	US- PGPUB ; USPAT	2006/06/0 5 18:09	

	<b>Error Definition</b>	<b>Err ors</b>
<b>21</b>		
<b>22</b>		
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<b>24</b>		
<b>25</b>		

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
26	BRS	L26	1	25 and subsampl\$3 and symbol	US-PGPUB ; USPAT ; EPO; JPO	2006/06/05 18:10	
27	BRS	L27	3	((EUNG-BAE) near2 (KIM)) .INV.	US-PGPUB ; USPAT	2006/06/05 18:10	

	<b>Error Definition</b>	<b>Err ors</b>
<b>26</b>		
<b>27</b>		